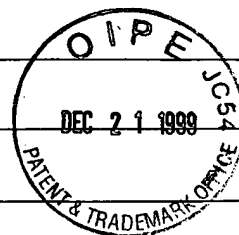


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.061DV1	APPLICATION NO. 09/397,952
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT AHMAD	
		FILING DATE September 17, 1999	GROUP 2814



## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
SR	4,839,301	06/13/89	Lee			
	4,996,081	2/26/91	Ellul, et al.			
	5,057,499	10/15/91	Lowrey et al.			
	5,073,509	12/17/91	Lee			
	5,177,027	1/5/93	Lowrey et al.			
	5,240,874	8/31/93	Roberts			
	5,264,724	11/23/93	Brown et al.			
	5,266,510	11/30/93	Lee			
	5,272,367	12/21/93	Dennison et al.			
	5,341,016	08/23/94	Prall et al.			
	5,345,104	09/06/94	Prall et al.			
	5,349,494	9/20/94	Ando			
	5,360,769	11/01/94	Thakur et al.			
	5,376,593	12/27/94	Sandhu et al.			
	5,378,641	1/3/95	Cheffings			
	5,393,683	2/28/95	Mathews, et al.			
	5,405,791	4/11/95	Ahmad et al.			
	5,407,870	4/18/95	Okada et al.			
	5,429,972	7/4/95	Anjum et al.			
	5,463,234	10/95	Toriumi et al.	257	410	
	5,472,896	12/05/95	Chen et al.			
	5,811,865	9/98	Hodges et al.	257	411	5/94

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
SR	Shimizu, et al. "Impact of Surface Proximity Gettering and Nitrided Oxide Side-Wall Spacer by Nitrogen Implantation on Sub-Quarter Micron CMOS LDD FETs", IEDM 95, pp. 859-62 (1995).

W:\DOCS\ASA\ASA-4628.DOC 121699

EXAMINER	DATE CONSIDERED
	July 18/2002

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.